MSK4005D

Schottky Barrier Diode

FEATURES

- Low forward voltage
- Thin & leadless package for space saving

DFN1006(0402)

MECHANICAL CHARACTERISTICS

- Case: DFN1006(0402) mold package
- Terminal: Gold plated, solderable per MIL-STD-750, method 2026
- Weight: 0.001 gram(approx.)

Maxim Rating And ELECTRICAL CHARACTERISTICS (at TA=25℃ unless otherwise noted)

Parameter	Condition	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		VRRM			35	V
Reverse voltage		VR			30	V
Average forward current		Io			100	mA
Forward current surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	IFSM			1	A
Storage/Operation temperature		T_{Sgt}	-40		125	℃
Junction temperature		T_J			125	℃
Forward voltage	IF=10mA IF=20mA	VF			0.29 0.30	V
Reverse current	VR=30V	IR			30	uA

Typical Characteristics

Fig.1-forward characteristics

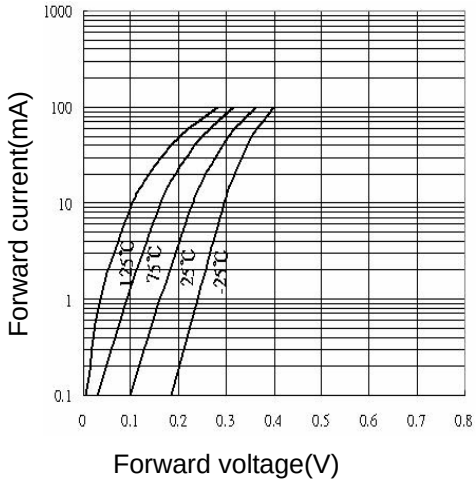


Fig.2-Reverse characteristics

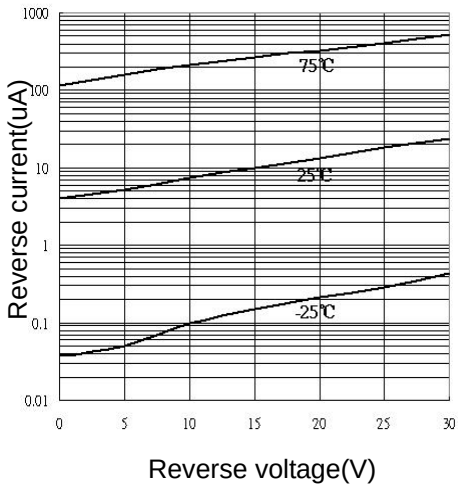


Fig.3 - Capacitance between terminals characteristics

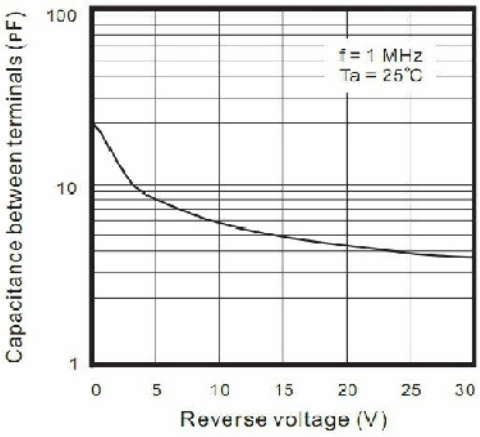


Fig.4 - Current derating curve

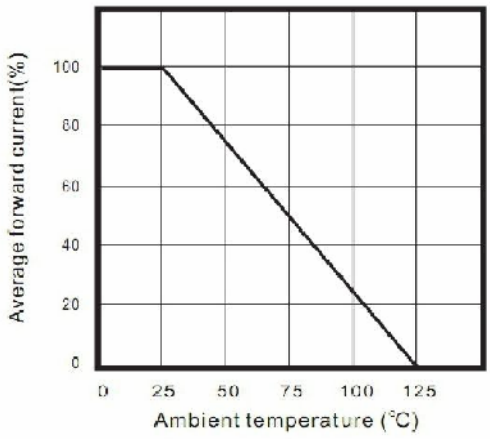


Fig. 5 - VF Dispersion map

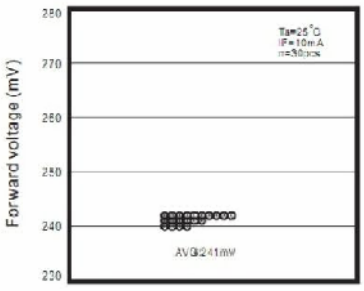


Fig. 6 - IR Dispersion map

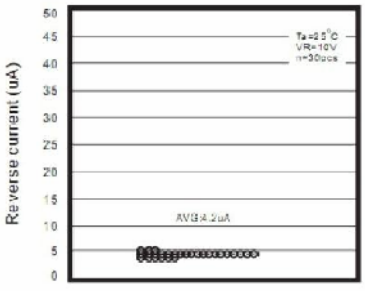
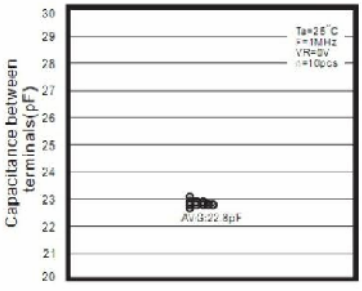


Fig. 7 - CT Dispersion map



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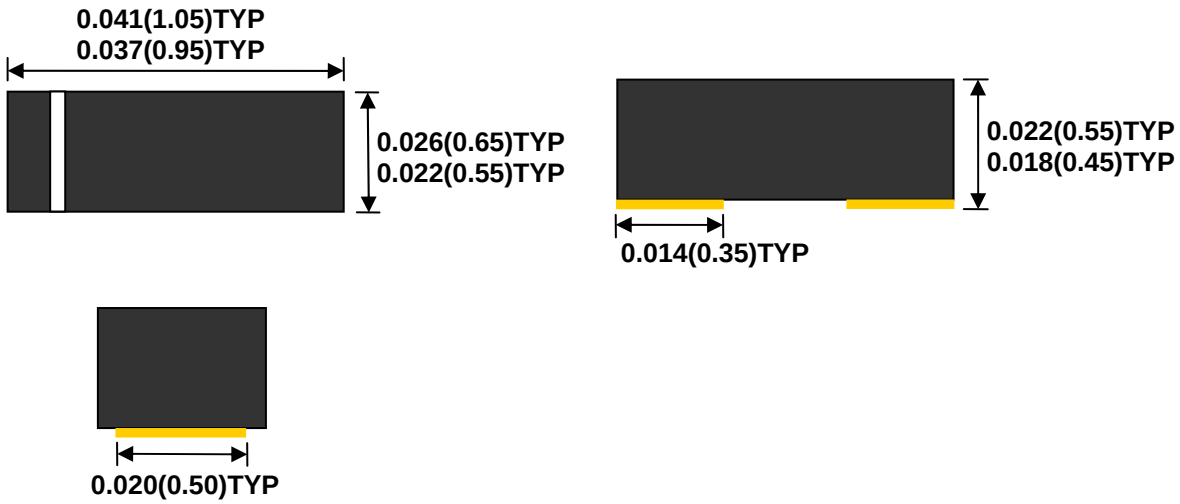
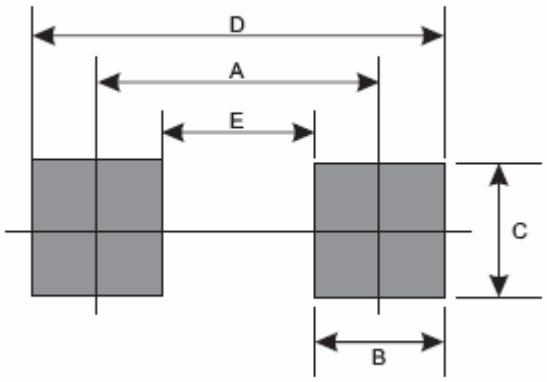


Dimensions in inches and (millimeter)

RECOMMENDED SOLDERING FOOTPRINT



Reflow Soldering

Product Size	Dimension/ mm				
	A	B	C	D	E
DFN1006	0.750	0.500	0.700	1.250	0.250
	0.030″	0.020″	0.028″	0.049″	0.010″